PM50RL1C060

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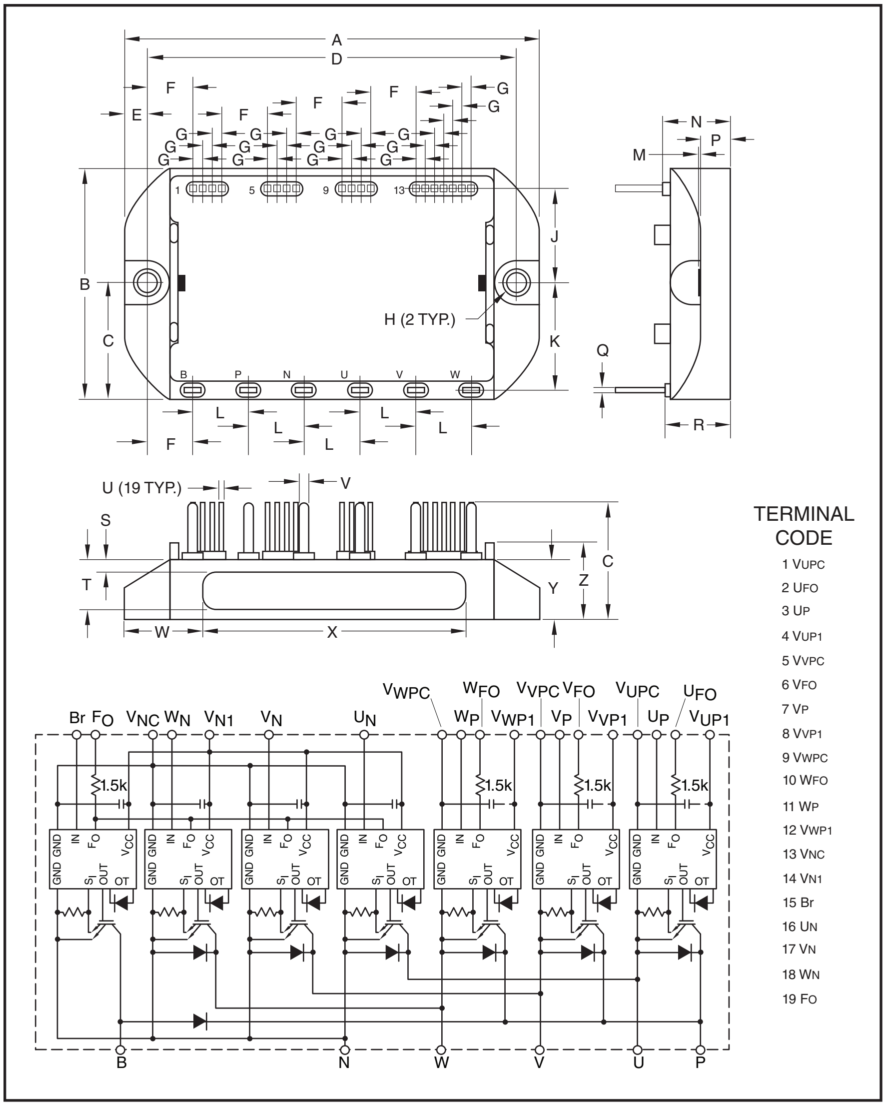
Intellimod™ L1-Series

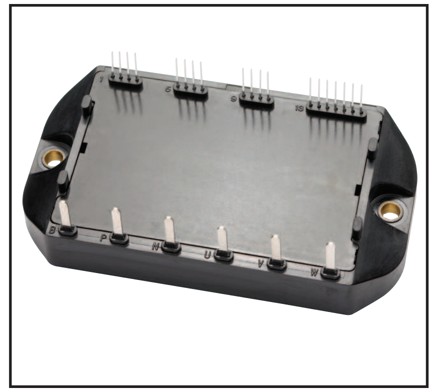
Three Phase
IGBT Inverter + Brake
50 Amperes/600 Volts



Outline Drawing and Circuit Diagram

Dim.	Inches	Millimeters
A	3.54	90.0
B	1.97	50.0
C	0.98	25.0
D	3.5	80.0
E	0.2	5.0
F	0.4	10.0
G	0.08	2.0
H	0.17 Dia.	4.3 Dia.
J	0.8	20.5
K	0.9	23.0
L	0.5	12.0
M	0.012	0.3

Dim.	Inches	Millimeters
N	0.58	14.6
P	0.26	6.7
Q	0.02	0.5
R	0.56	14.2
S	0.1±0.02	2.5±0.5
T	0.31	8.0
U	0.02 Sq.	0.5 Sq.
V	0.08	2.0
W	0.69±0.02	17.5±0.5
X	2.20	55.0
Y	0.52	13.0
Z	0.65	16.5



Description:

Powerex Intellimod™ Intelligent Power Modules are isolated base modules designed for power switching applications operating at frequencies to 20kHz. Built-in control circuits provide optimum gate drive and protection for the IGBT and free-wheel diode power devices.

Features:

- ☐ Complete Output Power Circuit
- ☐ Gate Drive Circuit
- ☐ Protection Logic
  - – Short Circuit
  - – Over Temperature Using On-chip Temperature Sensing
  - – Under Voltage
- ☐ Low Loss Using Full Gate CSTBT™ IGBT Chip

Applications:

- ☐ Inverters
- ☐ UPS
- ☐ Motion/Servo Control
- ☐ Power Supplies

Ordering Information:

Example: Select the complete part number from the table below -i.e. PM50RL1C060 is a 600V, 50 Ampere Intellimod™ Intelligent Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 10)
PM	50	60

Absolute Maximum Ratings, T_j = 25°C unless otherwise specified

Characteristics	Symbol	PM50RL1C060	Units
Power Device Junction Temperature	T_j	-20 to 150	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Mounting Torque, M4 Mounting Screws	—	15	in-lb
Module Weight (Typical)	—	150	Grams
Supply Voltage, Surge (Applied between P - N)	$V_{CC(surge)}$	500	Volts
Self-protection Supply Voltage Limit (Short Circuit protection Capability)*	$V_{CC(prot.)}$	400	Volts
Isolation Voltage, AC 1 minute, 60Hz Sinusoidal	V_{ISO}	2500	Volts

IGBT Inverter Sector

Collector-Emitter Voltage (V_D = 15V, V_{CIN} = 15V)	V_{CES}	600	Volts
Collector Current (T_C = 25°C) (Note 1)	$\pm I_C$	50	Amperes
Peak Collector Current (T_C = 25°C)	$\pm I_{CP}$	100	Amperes
Collector Dissipation (T_C = 25°C) (Note 1)	P_C	168	Watts

IGBT Brake Sector

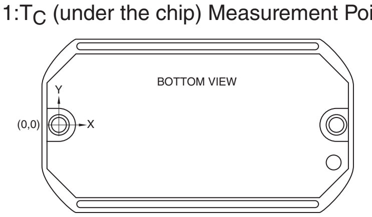
Collector-Emitter Voltage (V_D = 15V, V_{CIN} = 15V)	V_{CES}	600	Volts
Collector Current (T_C = 25°C) (Note 1)	$\pm I_C$	50	Amperes
Peak Collector Current (T_C = 25°C)	$\pm I_{CP}$	100	Amperes
Collector Dissipation (T_C = 25°C) (Note 1)	P_C	168	Watts
Diode Forward Current (T_C = 25°C)	I_F	50	Amperes
Diode Rated DC Reverse Voltage (T_C = 25°C)	$V_{R(DC)}$	600	Volts

Control Sector

Supply Voltage (Applied between V_{UP1}-V_{UPC}, V_{VP1}-V_{VPC}, V_{WP1}-V_{WPC}, V_{N1}-V_{NC})	V_D	20	Volts
Input Voltage (Applied between U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC}, U_N- V_N- W_N-Br-V_{NC})	V_{CIN}	20	Volts
Fault Output Supply Voltage (Applied between U_{FO}-V_{UPC}, V_{FO}-V_{VPC}, W_{FO}-V_{WPC}, F_O-V_{NC})	V_{FO}	20	Volts
Fault Output Current (U_{FO}, V_{FO}, W_{FO}, F_O Terminals)	I_{FO}	20	mA

*VD = 13.5 ~ 16.5V, Inverter Part, T_j = 125°C

Note 1:T_C (under the chip) Measurement Point



Arm	UP		VP		WP		UN		VN		WN		Br	
Axis	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi
X	49.0	49.0	35.0	35.0	21.0	21.0	42.0	42.0	28.0	28.0	14.0	14.0	64.0	68.2
Y	2.8	-3.3	2.8	-3.3	2.8	-3.3	-7.3	-1.2	-7.3	-1.2	-5.3	0.8	3.9	-4.6

Electrical and Mechanical Characteristics, T_j = 25°C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
IGBT Inverter Sector						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_D = 15V, V_{CIN} = 0V, I_C = 50A, T_j = 25°C	—	1.65	—	Volts
		V_D = 15V, V_{CIN} = 0V, I_C = 50A, T_j = 125°C	—	1.65	—	Volts
Diode Forward Voltage	V_{EC}	$-I_C$ = 50A, V_{CIN} = 15V, V_D = 15V	—	1.7	—	Volts
Inductive Load Switching Times	t_{on}	V_D = 15V, V_{CIN} = 0 ⇔ 15V, V_{CC} = 300V, I_C = 50A, T_j = 125°C	—	1.0	—	µs
	t_{rr}		—	0.2	—	µs
	$t_{C(on)}$		—	0.4	—	µs
	t_{off}		—	1.0	—	µs
	$t_{C(off)}$		—	0.3	—	µs
Collector-Emitter Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, V_D = 15V, T_j = 25°C	—	—	1.0	mA
		$V_{CE} = V_{CES}$, V_D = 15V, T_j = 125°C	—	—	10	mA
IGBT Brake Sector						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_D = 15V, V_{CIN} = 0V, I_C = 50A, T_j = 25°C	—	1.65	—	Volts
		V_D = 15V, V_{CIN} = 0V, I_C = 50A, T_j = 125°C	—	1.65	—	Volts
Forward Voltage	V_{FM}	I_F = 50A	—	1.7	—	Volts
Collector-Emitter Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, V_D = 15V, T_j = 25°C	—	—	1.0	mA
		$V_{CE} = V_{CES}$, V_D = 15V, T_j = 125°C	—	—	10	mA
Control Sector						
Circuit Current	I_D	V_D = 15V, V_{CIN} = 15V, V_{N1}-V_{NC}	—	20	30	mA
		V_D = 15V, V_{CIN} = 15V, V_{*P1}-V_{*PC}	—	5	10	mA
Input ON Threshold Voltage	$V_{th(on)}$	Applied between U_P-V_{UPC},	1.2	1.5	1.8	Volts
Input OFF Threshold Voltage	$V_{th(off)}$	V_P-V_{VPC}, W_P-V_{WPC}, U_N- V_N- W_N-Br-V_{NC}	1.7	2.0	2.3	Volts
Short Circuit Trip Level	SC	Inverter Part	100	—	—	Amperes
(-20°C ≤ T_j ≤ 125°C, V_D = 15V)		Brake Part	100	—	—	Amperes
Short Circuit Current Delay Time	$t_{off(SC)}$	V_D = 15V	—	0.2	—	µs
Over Temperature Protection	OT	Trip Level	135	145	—	°C
(Detect T_j of IGBT Chip)	OT_R	Reset Level	—	125	—	°C
Supply Circuit Under-voltage Protection	UV	Trip Level	11.5	12.0	12.5	Volts
(-20 ≤ T_j ≤ 125°C)	UV_R	Reset Level	12.0	12.5	13.0	Volts
Fault Output Current*	$I_{FO(H)}$	V_D = 15V, V_{CIN} = 15V	—	—	0.01	mA
	$I_{FO(L)}$	V_D = 15V, V_{CIN} = 15V	—	10	15	mA
Minimum Fault Output Pulse Width*	t_{FO}	V_D = 15V	1.0	1.8	—	ms

*Fault output is given only when the internal SC, OT and UV protections schemes of either upper or lower arm device operates to protect it.

Electrical and Mechanical Characteristics, T_j = 25°C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units

Thermal Characteristics, T_j = 25°C unless otherwise specified

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Units
Junction to Case Thermal Resistance	$R_{th(j-c)Q}$	IGBT (Per 1 Element) (Note 1)	—	—	0.74*	°C/Watt
Inverter Part	$R_{th(j-c)D}$	FWDi (Per 1 Element) (Note 1)	—	—	1.28*	°C/Watt
Junction to Case Thermal Resistance	$R_{th(j-c)Q}$	IGBT (Note 1)	—	—	0.74*	°C/Watt
Brake Part	$R_{th(j-c)D}$	FWDi (Note 1)	—	—	1.28*	°C/Watt
Contact Thermal Resistance	$R_{th(c-f)}$	Case to Fin Per Module, Thermal Grease Applied (Note 1)	—	—	0.085	°C/Watt

Recommended Conditions for Use

Characteristic	Symbol	Condition	Value	Units
Supply Voltage	V_{CC}	Applied across P-N Terminals	≤400	Volts
Control Supply Voltage**	V_D	Applied between V_{UP1}-V_{UPC}, V_{VP1}-V_{VPC}, V_{WP1}-V_{WPC}, V_{N1}-V_{NC}	15.0 ±1.5	Volts
Input ON Voltage	$V_{CIN(on)}$	Applied between U_P-V_{UPC},	≤0.8	Volts
Input OFF Voltage	$V_{CIN(off)}$	V_P-V_{VPC}, W_P-V_{WPC}, U_N- V_N- W_N-Br-V_{NC}	≥9.0	Volts
PWM Input Frequency	f_{PWM}	—	≤20	kHz
Arm Shoot-through Blocking Time	t_{DEAD}	Input Signal	≥2.0	μs

* If you use this value, $R_{th(f-a)}$ should be measured just under the chips.
** With ripple satisfying the following conditions: dv/dt swing ≤ ±5V/μs, Variation ≤ 2V peak to peak.